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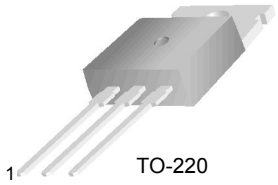
October 2008

FJP3305

High Voltage Fast-Switching NPN Power Transistor

- High Voltage Capability
- High Switching Speed
- Suitable for Electronic Ballast and Switching Regulator



TO-220

1.Base 2.Collector 3.Emitter

Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	700	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current (DC)	4	A
I_{CP}	Collector Current (Pulse)	8	A
I_B	Base Current	2	A
P_C	Collector Dissipation (T_C = 25°C)	75	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	-65 ~ 150	°C

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
BV_{CBO}	Collector-Base Breakdwon Voltage	I_C = 500μA, I_E = 0	700			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 5mA, I_B = 0	400			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 500μA, I_C = 0	9			V
I_{CBO}	Collector Cut-off Current	V_{CB} = 700V, I_E = 0			1	μA
I_{EBO}	Emitter Cut-off Current	V_{EB} = 9V, I_C = 0			1	μA
h_{FE1} h_{FE2}	DC Current Gain *	V_{CE} = 5V, I_C = 1A V_{CE} = 5V, I_C = 2A	19 8		35 40	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 1A, I_B = 0.2A I_C = 2A, I_B = 0.5A I_C = 4A, I_B = 1A			0.5 0.6 1.0	V V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 1A, I_B = 0.2A I_C = 2A, I_B = 0.5A			1.2 1.6	V V
f_T	Current Gain Bandwidth Product	V_{CE} = 10V, I_C = 0.5A	4			MHz
C_{ob}	Output Capacitance	V_{CB} = 10V, f = 1MHz		65		pF
t_{ON}	Turn On Time	V_{CC} = 125V, I_C = 2A I_{B1} = -I_{B2} = 0.4A R_L = 62.5Ω			0.8	μs
t_{STG}	Storge Time				4.0	μs
t_F	Fall Time				0.9	μs

* Pulse Test: PW ≤ 300μs, Duty Cycle ≤ 2%

h_{FE} Classification

Classification	H1	H2
h_{FE1}	19 ~ 28	26 ~ 35

Typical Performance Characteristics

Figure 1. Static Characteristic

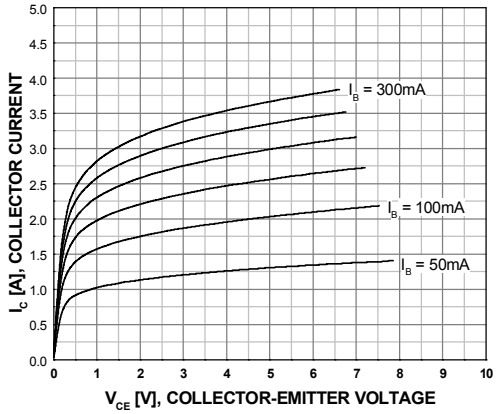


Figure 2. DC Current Gain (R-Grade)

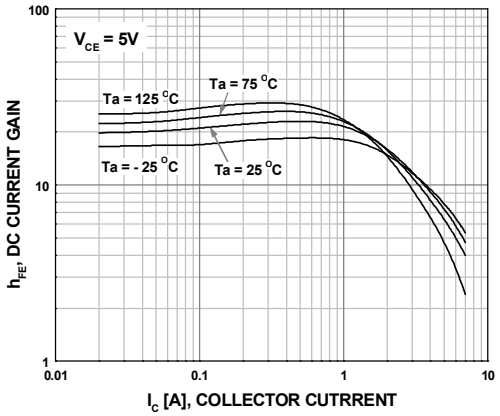


Figure 3. DC Current Gain (O-Grade)

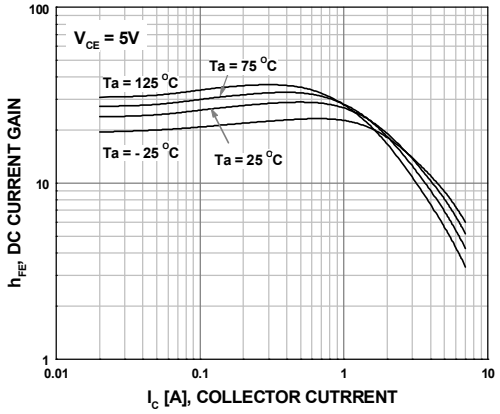


Figure 4. Saturation Voltage (R-Grade)

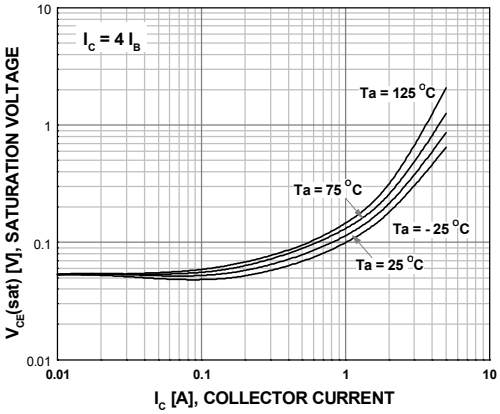


Figure 5. Saturatin Voltage (O-Grade)

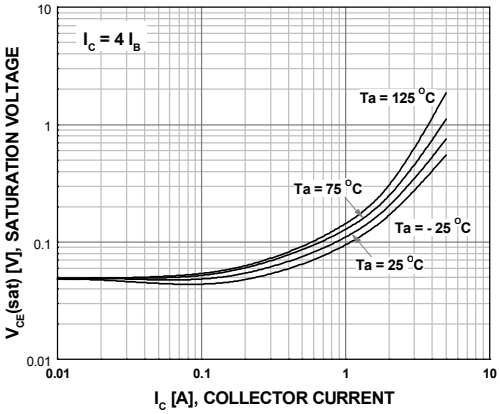
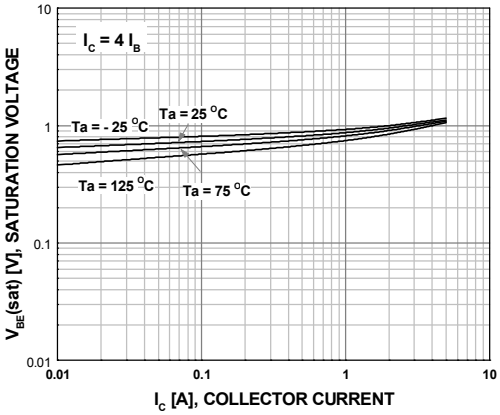


Figure 6. Saturation Voltage (R-Grade)



Typical Performance Characteristics (Continued)

Figure 7. Saturation Voltage (O-Grade)

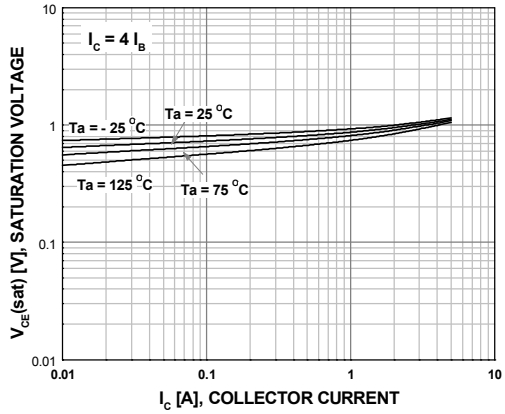


Figure 8. Switching Time

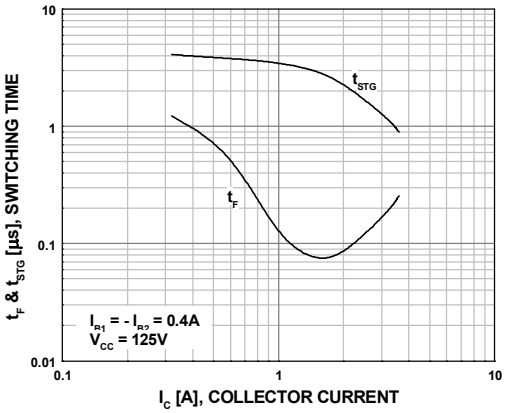


Figure 9. Reverse Biased Safe Operating Area

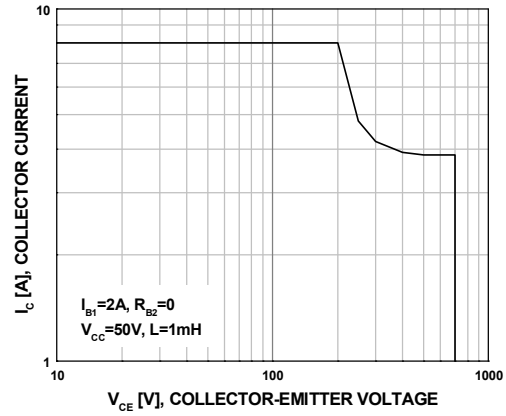


Figure 10. Forward Biased Safe Operating Area

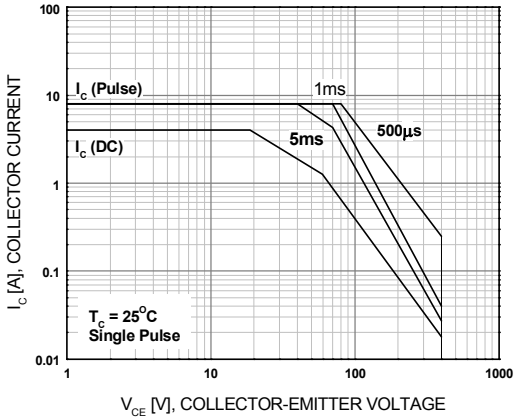
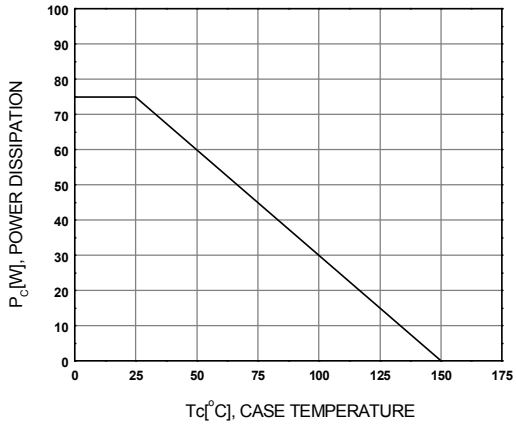
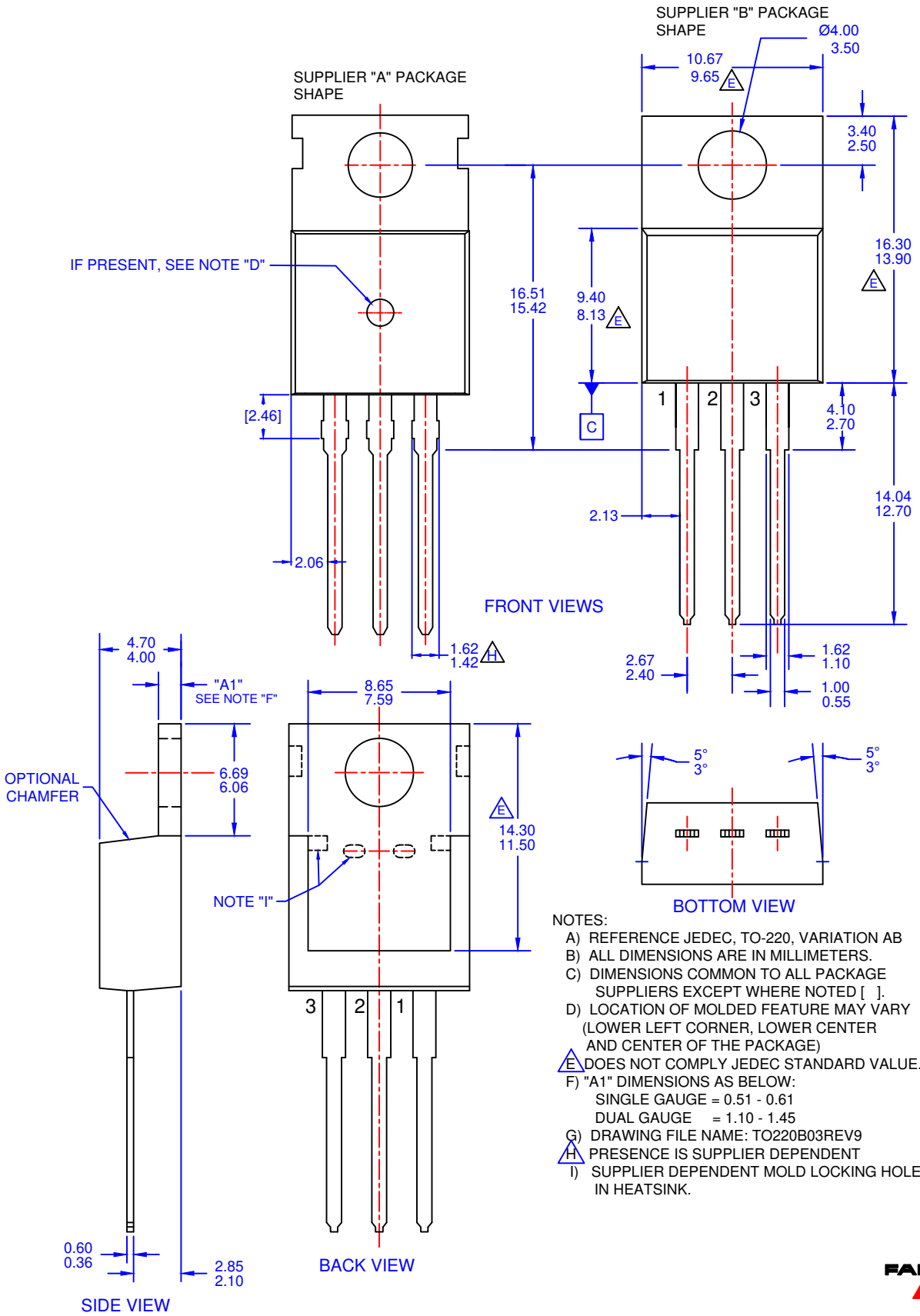


Figure 11. Power Derating





NOTES:

A) REFERENCE JEDEC, TO-220, VARIATION AB
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [ ].
D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
E) DOES NOT COMPLY JEDEC STANDARD VALUE.
F) "A1" DIMENSIONS AS BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1.10 - 1.45
G) DRAWING FILE NAME: TO220B03REV9
H) PRESENCE IS SUPPLIER DEPENDENT
I) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

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